

**ABSTRACT OF THE DISCLOSURE**

This invention relates to silicon precursor compositions for forming silicon-containing films by low temperature (e.g.,  $< 300^{\circ}\text{C}$ ) chemical vapor deposition processes for fabrication of ULSI devices and device structures. Such silicon precursor compositions comprise at least one disilane derivative compound that is fully substituted with alkylamino and/or dialkylamino functional groups.